

April 1996



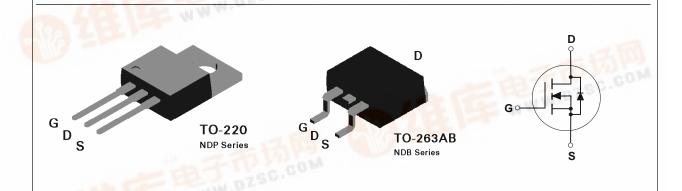
# NDP6060L / NDB6060L N-Channel Logic Level Enhancement Mode Field Effect Transistor

### **General Description**

These logic level N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulses in the avalanche and commutation modes. These devices are particularly suited for low voltage applications such as automotive, DC/DC converters, PWM motor controls, and other battery powered circuits where fast switching, low in-line power loss, and resistance to transients are needed.

# Features

- 48A, 60V.  $R_{DS(ON)} = 0.025\Omega @ V_{GS} = 5V.$
- Low drive requirements allowing operation directly from logic drivers. V<sub>GS(TH)</sub> < 2.0V.</li>
- Critical DC electrical parameters specified at elevated temperature.
- Rugged internal source-drain diode can eliminate the need for an external Zener diode transient suppressor.
- 175°C maximum junction temperature rating.
- High density cell design for extremely low R<sub>DS(ON)</sub>.
- TO-220 and TO-263 (D<sup>2</sup>PAK) package for both through hole and surface mount applications.

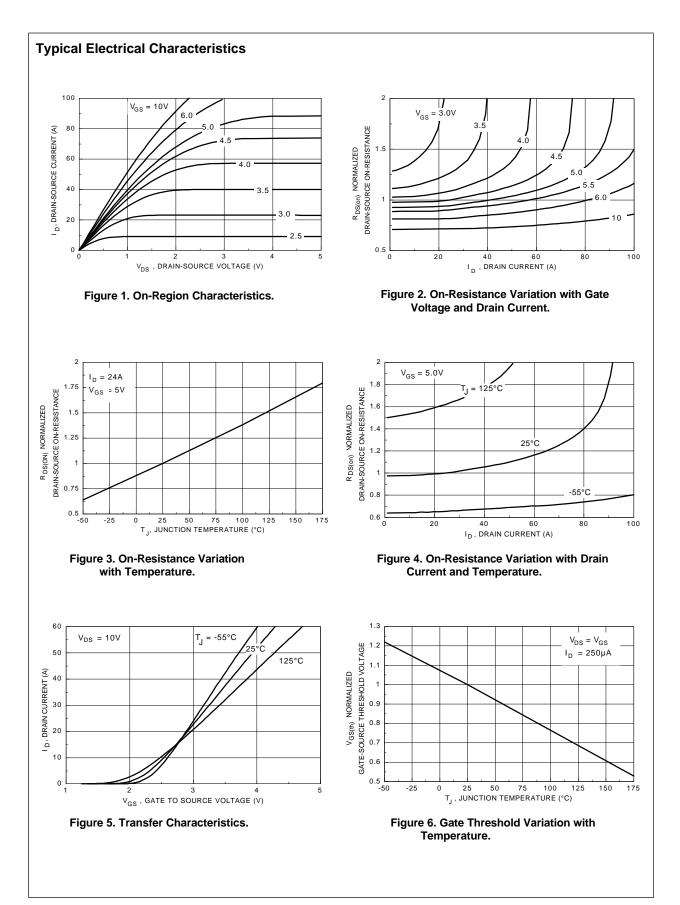


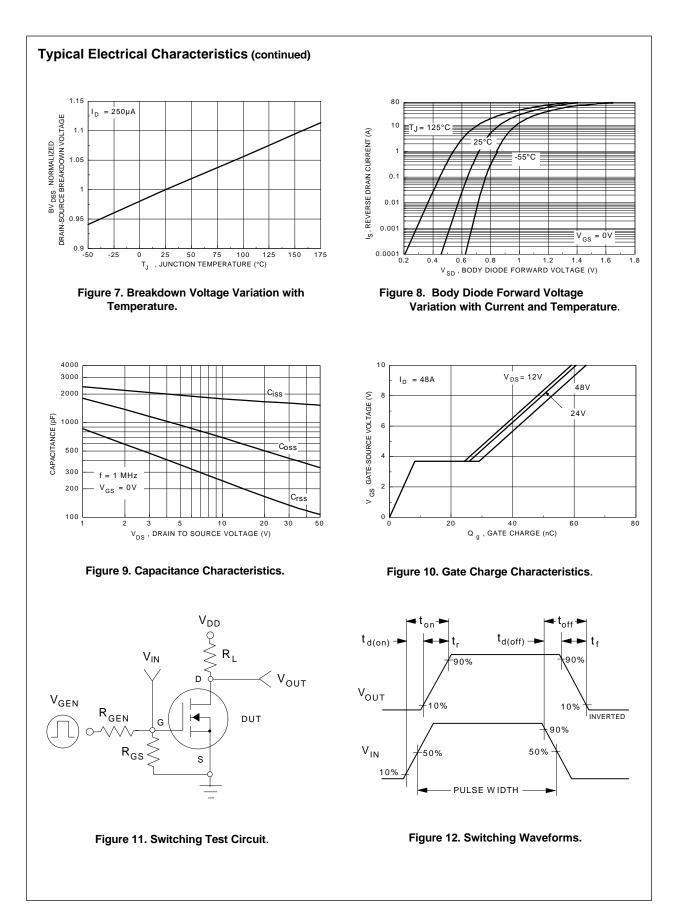
Symbol	Parameter	NDP6060L	NDB6060L	Units
V <sub>DSS</sub>	Drain-Source Voltage	60		V
V <sub>DGR</sub>	Drain-Gate Voltage ( $R_{GS} \le 1 \text{ M}\Omega$ )	60		
V <sub>GSS</sub>	Gate-Source Voltage - Continuous	±16		
	- Nonrepetitive ( $t_P < 50 \ \mu s$ )	±2	5	
I <sub>D</sub>	Drain Current - Continuous	48	3	А
	- Pulsed	14	4	
D	Total Power Dissipation @ $T_c = 25^{\circ}C$	10	0	W
	Derate above 25°C	0.6	7	W/°C
Г <sub>Ј</sub> ,Т <sub>STG</sub>	Operating and Storage Temperature	-65 to 175		
Г <sub>L</sub>	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	275		

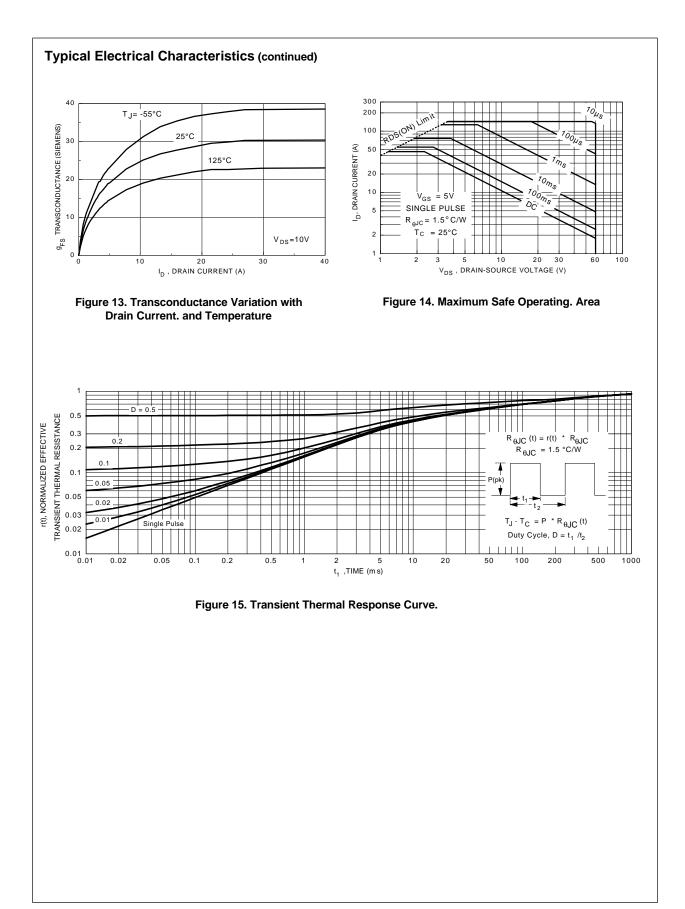
Symbol	Parameter	Conditions		Min	Тур	Max	Units
DRAIN-S	OURCE AVALANCHE RATINGS (Note 1)	·					
W <sub>DSS</sub>	Single Pulse Drain-Source Avalanche Energy	$V_{DD} = 25 \text{ V}, \text{ I}_{D} = 48 \text{ A}$				200	mJ
I <sub>AR</sub>	Maximum Drain-Source Avalanche Cu	rrent				48	А
OFF CH/	ARACTERISTICS						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, \text{ I}_{D} = 250 \mu\text{A}$		60			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}$				250	μA
			T <sub>J</sub> = 125°C			1	mA
I <sub>GSSF</sub>	Gate - Body Leakage, Forward	$V_{GS} = 16 \text{ V}, V_{DS} = 0 \text{ V}$				100	nA
I <sub>GSSR</sub>	Gate - Body Leakage, Reverse	$V_{GS} = -16 \text{ V},  V_{DS} = 0 \text{ V}$				-100	nA
ON CHAP	RACTERISTICS (Note 1)						
$V_{\text{GS(th)}}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$		1		2	V
			T <sub>J</sub> = 125°C	0.65		1.5	1
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	$V_{gs} = 5 V, I_{D} = 24 A$				0.025	Ω
			T <sub>J</sub> = 125°C			0.04	1
		$V_{GS} = 10 \text{ V}, I_{D} = 24 \text{ A}$	<u>-</u>			0.02	1
I <sub>D(on)</sub>	On-State Drain Current	$V_{GS} = 5 \text{ V}, V_{DS} = 10 \text{ V}$		48			Α
9 <sub>FS</sub>	Forward Transconductance	$V_{\rm DS} = 10 \text{ V}, I_{\rm D} = 24 \text{ A}$		10			S
DYNAMI	CCHARACTERISTICS	·					
C <sub>iss</sub>	Input Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1.0 MHz			1630	2000	pF
C <sub>oss</sub>	Output Capacitance				460	800	pF
C <sub>rss</sub>	Reverse Transfer Capacitance				150	400	pF
	NG CHARACTERISTICS (Note 1)					1	<u> </u>
t <sub>D(on)</sub>	Turn - On Delay Time	$V_{_{DD}} = 30 \text{ V}, \ \text{I}_{_{D}} = 48 \text{ A},$ $V_{_{GS}} = 5 \text{ V}, \ \text{R}_{_{\text{GEN}}} = 15 \Omega,$ $\text{R}_{_{\text{GS}}} = 15 \Omega$			15	30	nS
t <sub>r</sub>	Turn - On Rise Time				320	500	nS
t <sub>D(off)</sub>	Turn - Off Delay Time				49	100	nS
t <sub>f</sub>	Turn - Off Fall Time				161	300	nS
Q	Total Gate Charge	$V_{DS} = 48 \text{ V},$ $I_{D} = 48 \text{ A}, V_{GS} = 5 \text{ V}$			36	60	nC
Q <sub>qs</sub>	Gate-Source Charge				8.2		nC
Q <sub>gd</sub>	Gate-Drain Charge				21		nC

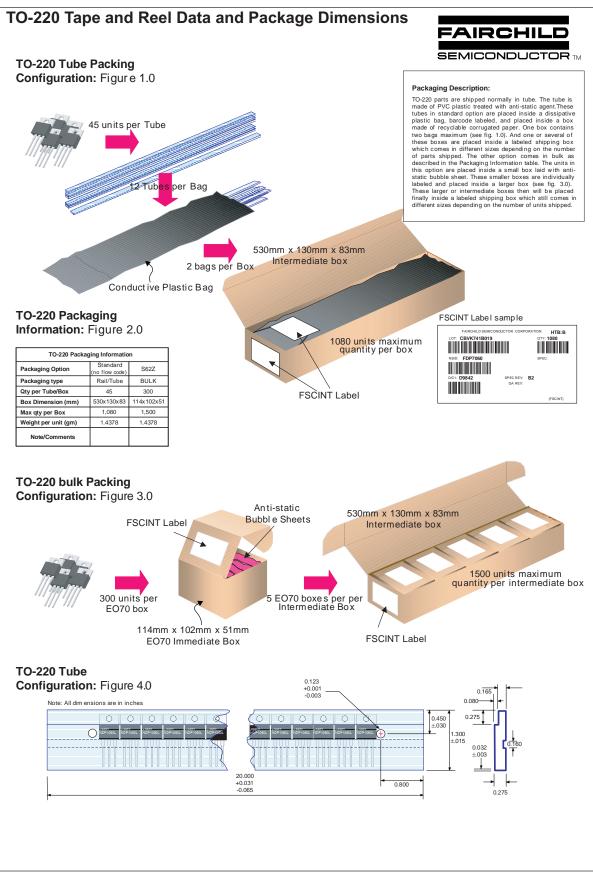
Symbol	Parameter	Conditions		Min	Тур	Max	Units
DRAIN-SO	DURCE DIODE CHARACTERISTICS	÷				•	
l <sub>s</sub>	Maximum Continuos Drain-Source Diode Forward Current				48	А	
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current				144	Α	
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	$V_{GS} = 0 V, I_{S} = 24 A (Note 1)$				1.3	V
			T <sub>J</sub> = 125°C			1.2	
t <sub>rr</sub>	Reverse Recovery Time	$V_{GS} = 0 V, I_F = 48 A,$ $dI_F/dt = 100 A/\mu s$		35	75	140	ns
I <sub>m</sub>	Reverse Recovery Current			2	3.6	8	А
THERMA	L CHARACTERISTICS						
R <sub>θJC</sub>	Thermal Resistance, Junction-to-Case				1.5	°C/W	
R <sub>θJA</sub>	Thermal Resistance, Junction-to-Ambient				62.5	°C/W	

Note: 1. Pulse Test: Pulse Width  $\leq$  300 µs, Duty Cycle  $\leq$  2.0%.

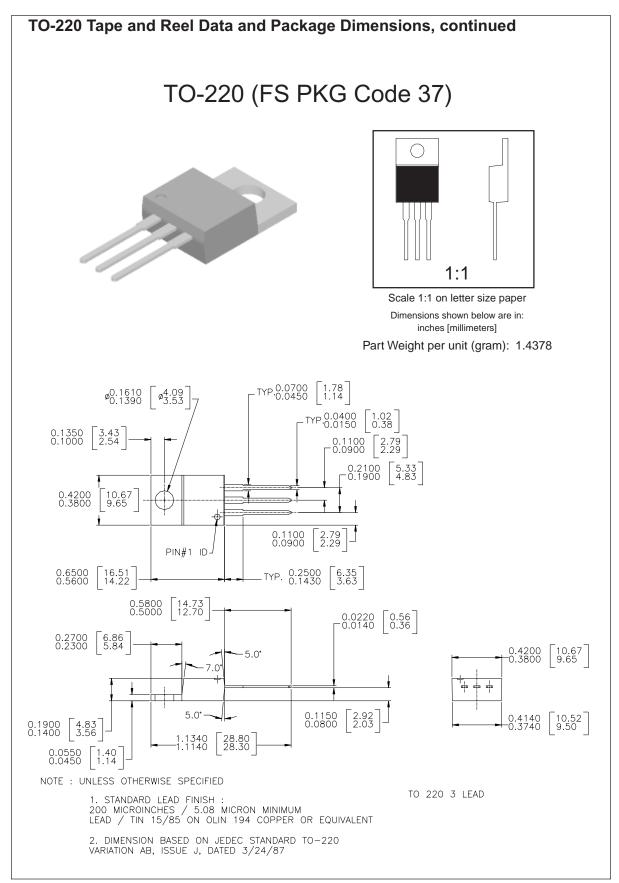


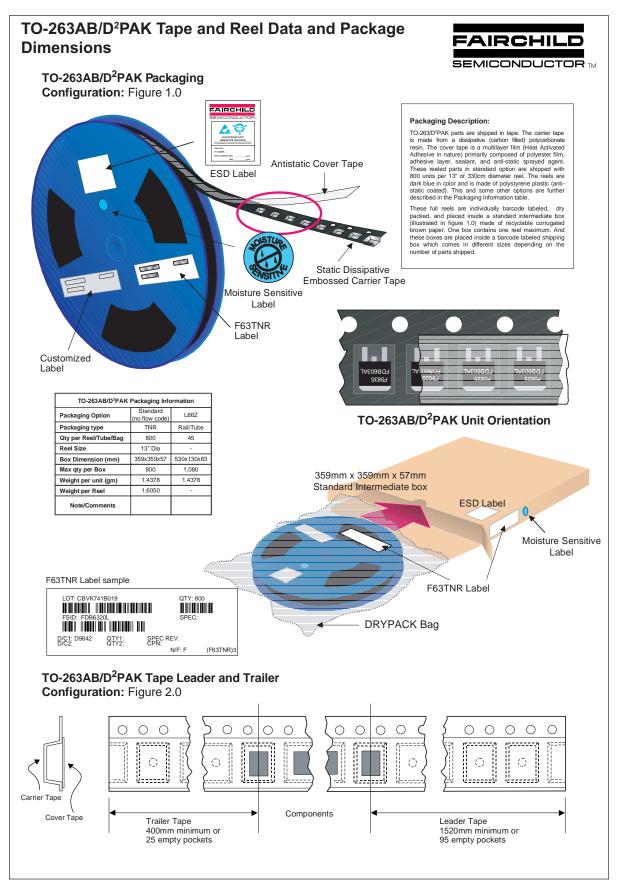


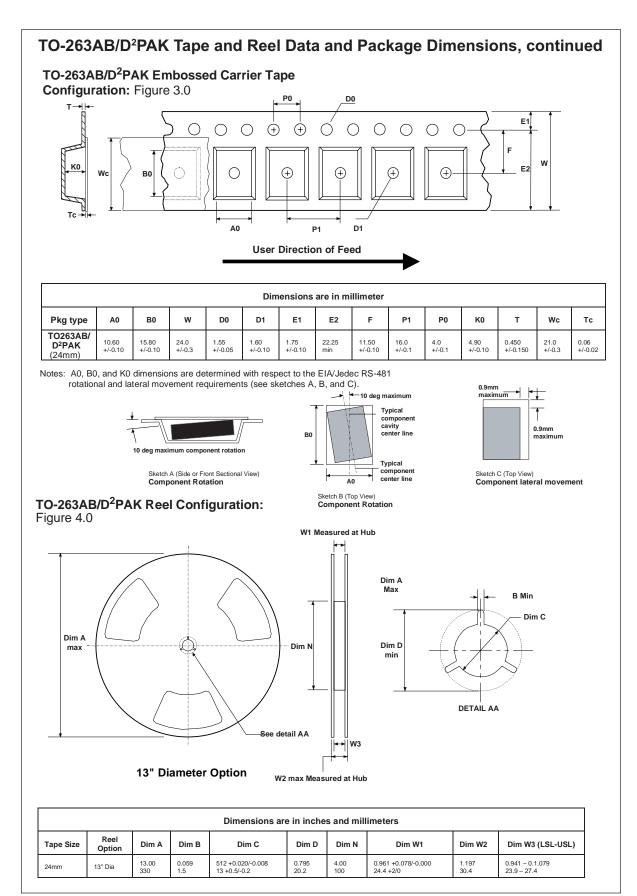


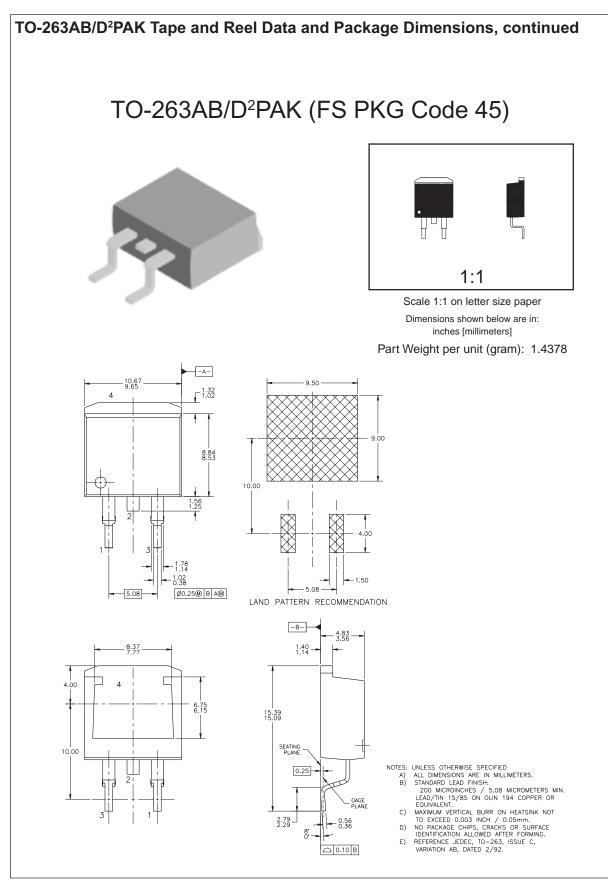


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